



ALPHA & OMEGA
SEMICONDUCTOR, LTD.

June 2004

AOD444, AOD444L (Green Product) N-Channel Enhancement Mode Field Effect Transistor

General Description	Features
<p>The AOD444 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.</p> <p>AOD444L (Green Product) is offered in a lead-free package.</p>	<p>V_{DS} (V) = 60V I_D = 12 A $R_{DS(ON)} < 60 \text{ m}\Omega$ ($V_{GS} = 10\text{V}$) $R_{DS(ON)} < 85 \text{ m}\Omega$ ($V_{GS} = 4.5\text{V}$)</p>

<p>TO-252 D-PAK</p> <p>Top View Drain Connected to Tab</p> <p>G D S</p>	
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Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted				
Parameter	Symbol	Maximum	Units	
Drain-Source Voltage	V_{DS}	60	V	
Gate-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current ^G	$T_C=25^\circ\text{C}$	12	A	
$T_C=100^\circ\text{C}$		12		
Pulsed Drain Current ^C	I_{DM}	30		
Avalanche Current ^C	I_{AR}	12	A	
Repetitive avalanche energy $L=0.1\text{mH}$ ^C	E_{AR}	23	mJ	
Power Dissipation ^B	$T_C=25^\circ\text{C}$	20	W	
		10		
Power Dissipation ^A	$T_A=25^\circ\text{C}$	2	W	
		1.3		
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	°C	

Thermal Characteristics				
Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$t \leq 10\text{s}$	$R_{\theta JA}$	17.4	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A			50	$^\circ\text{C/W}$
Maximum Junction-to-Case ^B	Steady-State	$R_{\theta JC}$	4	$^\circ\text{C/W}$
			7.5	

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=10\text{mA}, V_{GS}=0\text{V}$	60			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=48\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$		1	5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm20\text{V}$			100	nA
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1	2.4	3	V
$I_{D(\text{ON})}$	On state drain current	$V_{GS}=10\text{V}, V_{DS}=5\text{V}$	30			A
$R_{DS(\text{ON})}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=12\text{A}$		47	60	$\text{m}\Omega$
		$T_J=125^\circ\text{C}$		85		
		$V_{GS}=4.5\text{V}, I_D=6\text{A}$		67	85	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}, I_D=12\text{A}$		14		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.74	1	V
I_S	Maximum Body-Diode Continuous Current				12	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=30\text{V}, f=1\text{MHz}$		385	540	pF
C_{oss}	Output Capacitance			55		pF
C_{rss}	Reverse Transfer Capacitance			20		pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		1.35	2	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}, V_{DS}=30\text{V}, I_D=12\text{A}$		7.5	10	nC
$Q_g(4.5\text{V})$	Total Gate Charge			3.8	5	nC
Q_{gs}	Gate Source Charge			1.2		nC
Q_{gd}	Gate Drain Charge			1.9		nC
$t_{D(\text{on})}$	Turn-On Delay Time	$V_{GS}=10\text{V}, V_{DS}=30\text{V}, R_L=2.5\Omega, R_{\text{GEN}}=3\Omega$		4.2		ns
t_r	Turn-On Rise Time			3.4		ns
$t_{D(\text{off})}$	Turn-Off Delay Time			16		ns
t_f	Turn-Off Fall Time			2		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=12\text{A}, dI/dt=100\text{A}/\mu\text{s}$		27.6	35	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=12\text{A}, dI/dt=100\text{A}/\mu\text{s}$		30		nC

A: The value of R_{JJA} is measured with the device mounted on 1 in ² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on R_{JJA} and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B. The power dissipation P_D is based on $T_{J(\text{MAX})}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})}=175^\circ\text{C}$.

D. The R_{JJA} is the sum of the thermal impedance from junction to case R_{JJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(\text{MAX})}=175^\circ\text{C}$.

G. The maximum current rating is limited by bond-wires.

H. These tests are performed with the device mounted on 1 in ² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

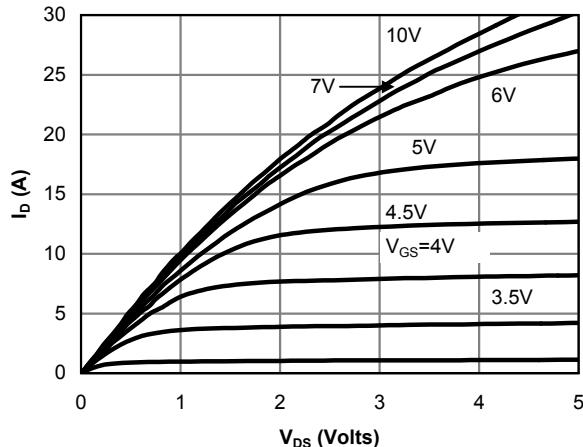


Fig 1: On-Region Characteristics

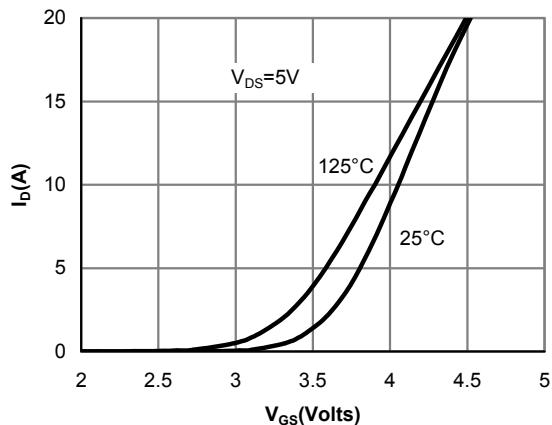


Figure 2: Transfer Characteristics

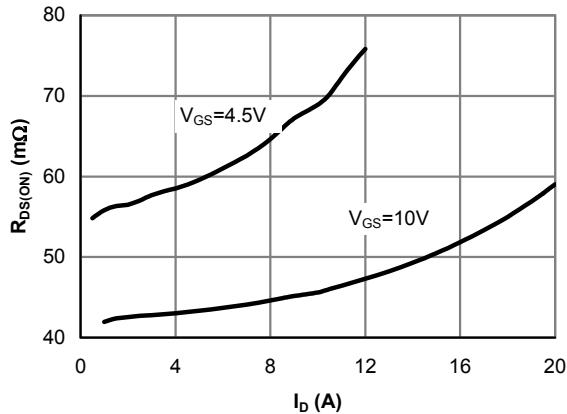


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

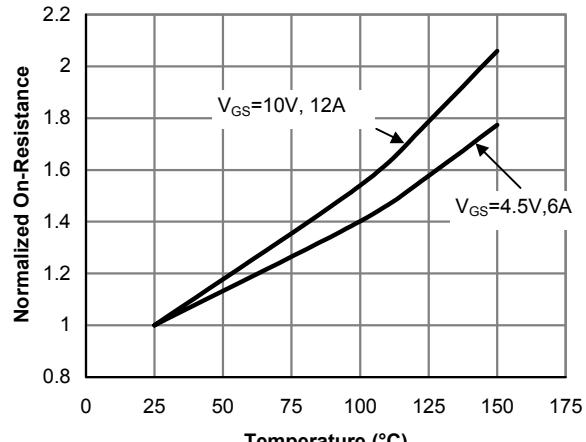


Figure 4: On-Resistance vs. Junction Temperature

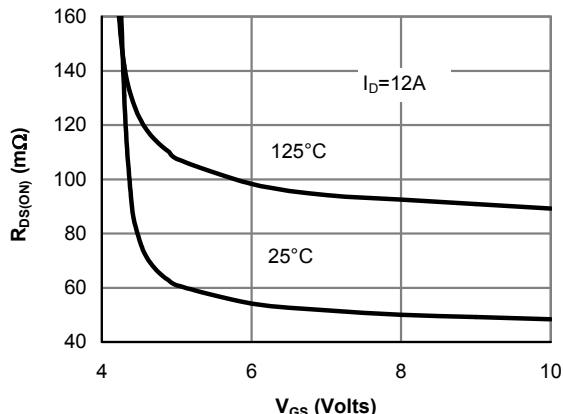


Figure 5: On-Resistance vs. Gate-Source Voltage

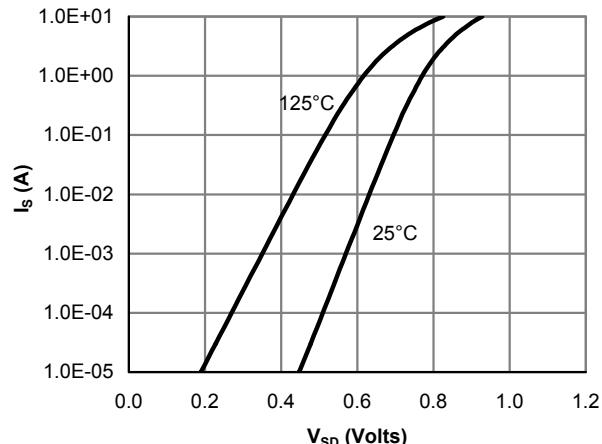
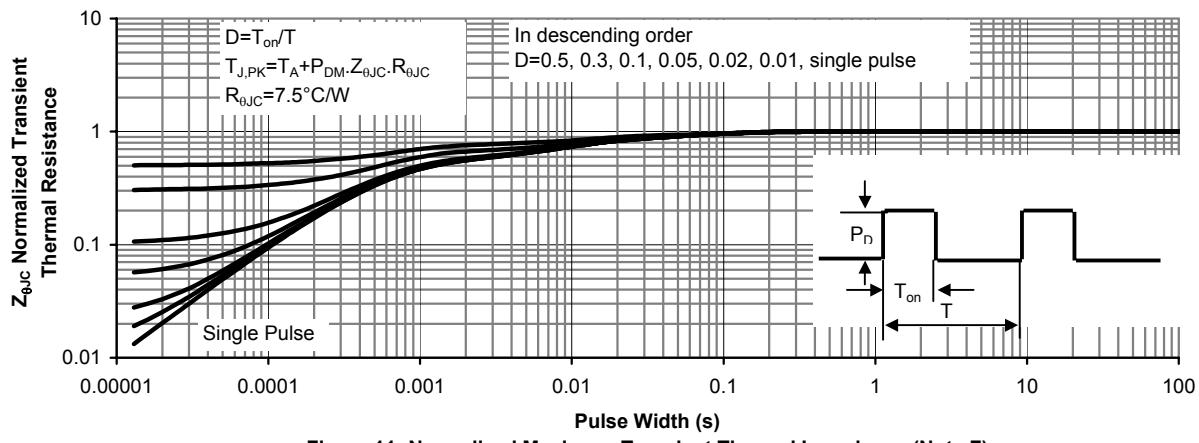
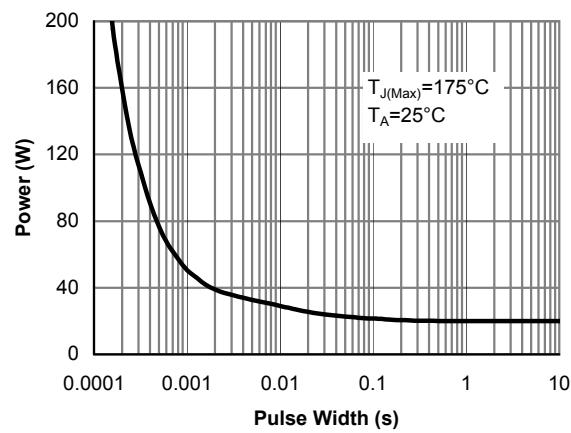
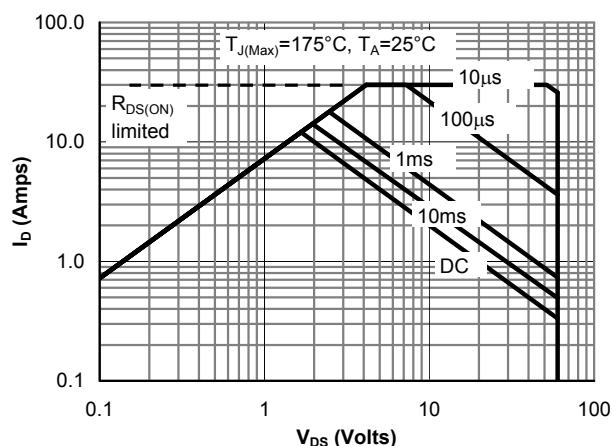
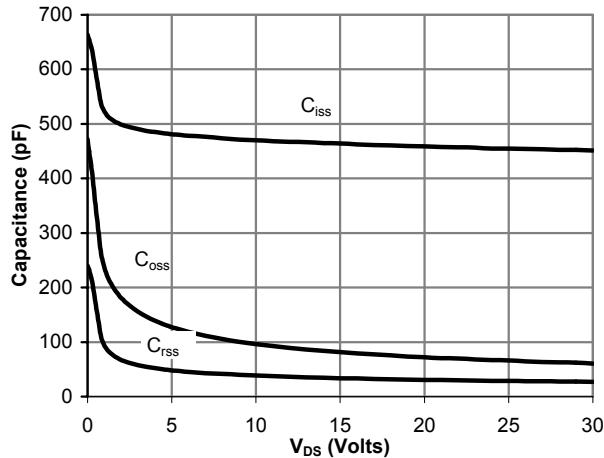
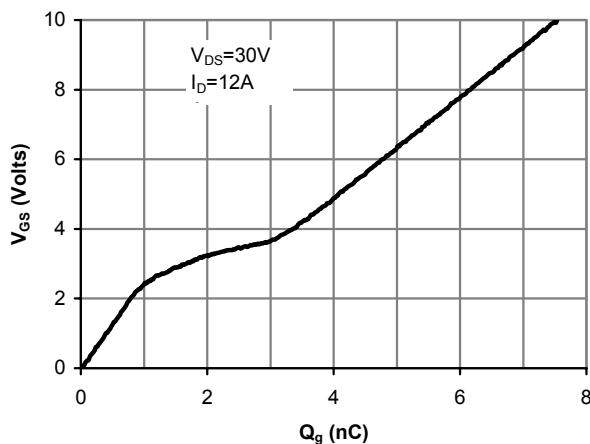


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



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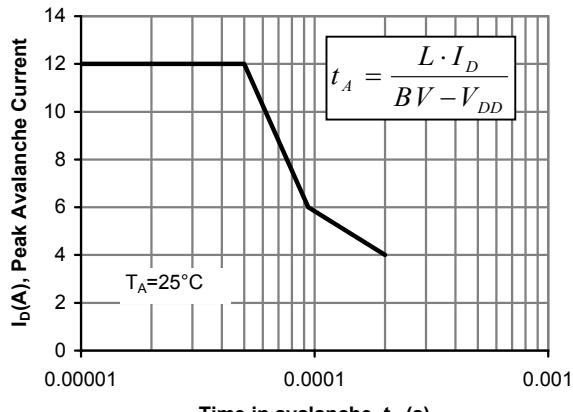


Figure 12: Single Pulse Avalanche capability

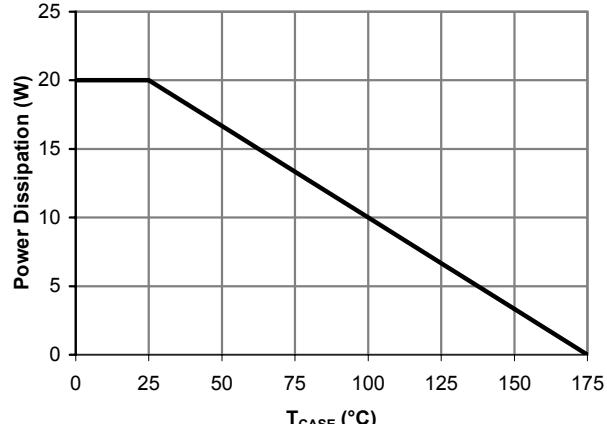


Figure 13: Power De-rating (Note B)

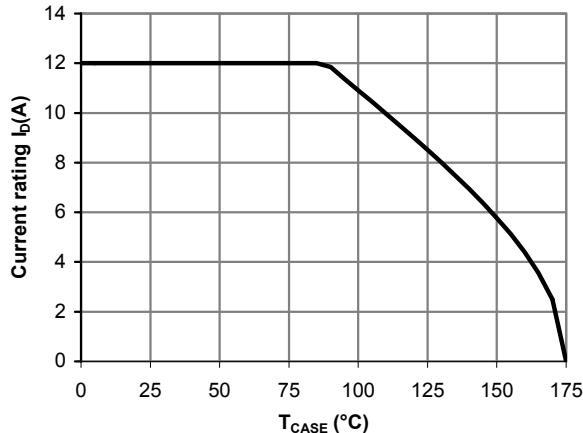


Figure 14: Current De-rating (Note B)

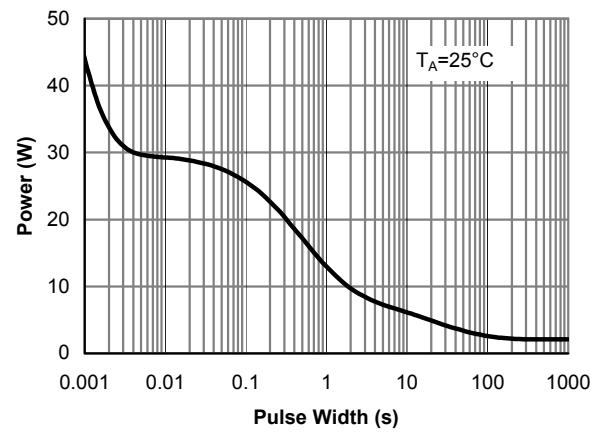


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note H)

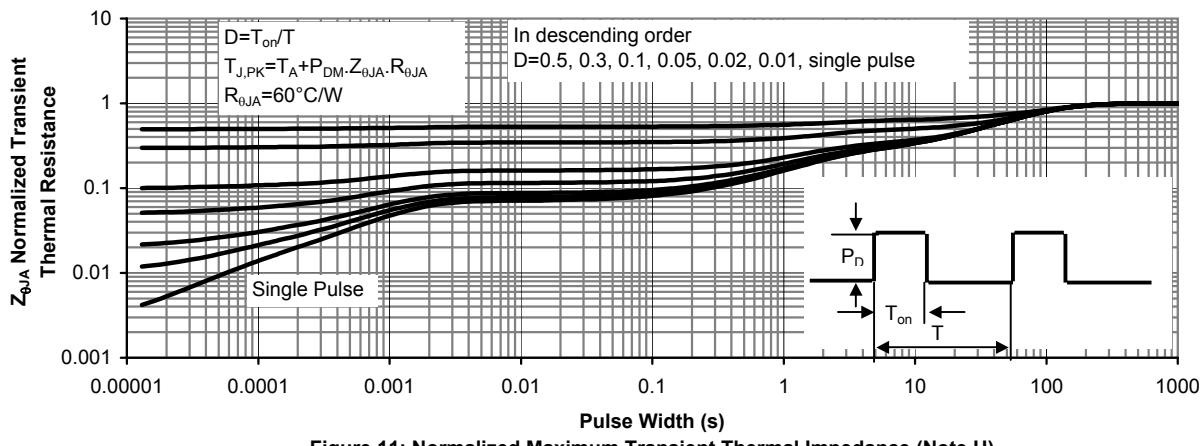
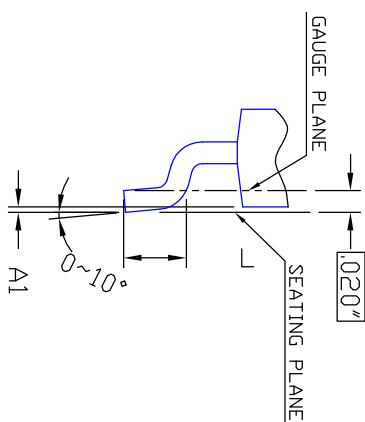
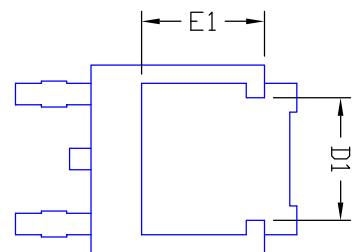
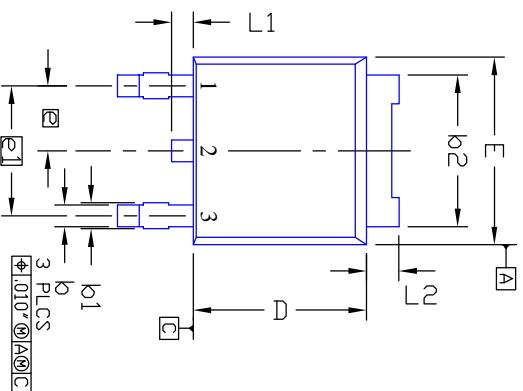


Figure 11: Normalized Maximum Transient Thermal Impedance (Note H)

- NOTE**
1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS
 2. DIMENSION L IS MEASURED IN GAGE PLANE
 3. TOLERANCE 0.10 mm UNLESS OTHERWISE SPECIFIED
 4. CONTROLLING DIMENSION IS MILLIMETER CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
 5. FOLLOWED FROM JEDEC TO-252 (AA)

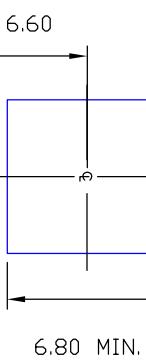
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DETAIL 'D'
SCALE: 1.5X

RECOMMENDED LAND PATTERN

6.25 MIN.



6.60
6.80 MIN.
1.50 MIN.
3.00 MIN.

2.286
4.572 BSC

UNIT: mm

DIMENSION IN MILLIMETERS		DIMENSIONS IN INCHES				
S Y M L B O B L	M MIN.	NOM.	MAX.	M MIN.	NOM.	M MAX.
A	2.235	2.286	2.388	0.088	0.090	0.094
A1	0.000	-----	0.102	0.000	-----	0.004
A2	0.889	-----	1.143	0.035	-----	0.045
b	0.686	0.762	0.889	0.027	0.030	0.035
b1	0.889	-----	1.143	0.035	-----	0.045
b2	5.207	4.45	5.461	0.205	-----	0.215
c	0.457	0.508	0.559	0.018	0.020	0.022
c1	0.483	-----	0.584	0.019	-----	0.023
D	5.969	6.096	6.223	0.235	0.240	0.245
D1	4.318	-----	5.334	0.170	-----	0.210
E	6.477	6.604	6.731	0.255	0.260	0.265
E1	4.318	-----	0.170	-----	-----	-----
e	2.286 BSC.	4.572 BSC.	0.090 BSC.	0.180 BSC.	0.090 BSC.	0.410
e1	2.286 BSC.	4.572 BSC.	0.090 BSC.	0.180 BSC.	0.090 BSC.	0.410
H	9.779	-----	10.414	0.385	-----	0.410
L	1.270	-----	2.032	0.050	-----	0.080
L1	0.635	-----	1.016	0.025	-----	0.040
L2	0.889	-----	1.270	0.035	-----	0.050

UNLESS OTHERWISE SPECIFIED
DIMENSIONS ARE IN INCHES

DECIMAL
ANGULAR
 \pm

XX ±
XXX ±
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INTERPRET DIM. AND TOL. PER
ASME Y14.5M - 1994

PRINTING IS SCALED TO FIT
DO NOT SCALE DRAWING

THIRD ANGLE
PROJECTION



ALPHA & OMEGA
SEMICONDUCTOR, LTD.



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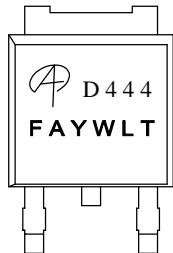
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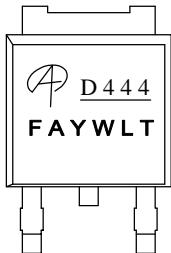
ALPHA & OMEGA
SEMICONDUCTOR, LTD.

Document No.	PD-00259
Version	rev B
Title	AOD444 Marking Description

DPAK PACKAGE MARKING DESCRIPTION



Standard product



Green product

NOTE:

- LOGO - AOS LOGO
D444 - PART NUMBER CODE.
F&A - FOUNDRY AND ASSEMBLY LOCATION
Y - YEAR CODE
W - WEEK CODE.
L T - ASSEMBLY LOT CODE

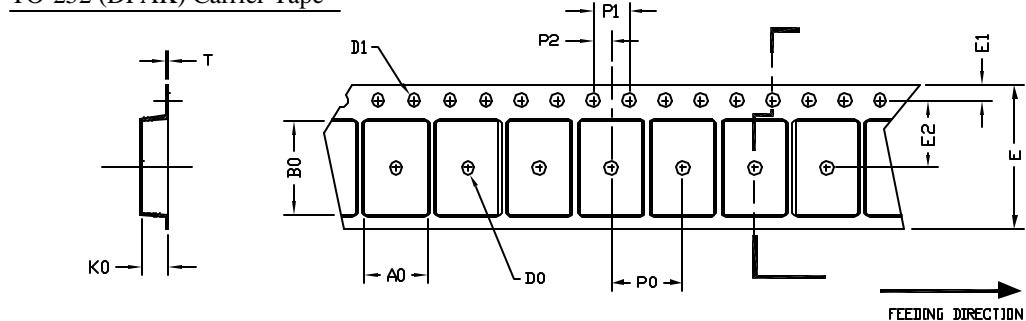
PART NO.	DESCRIPTION	CODE
AOD444	Standard product	D444
AOD444L	Green product	<u>D444</u>



ALPHA & OMEGA
SEMICONDUCTOR, INC.

TO-252 (DPAK)
Tape and Reel Data

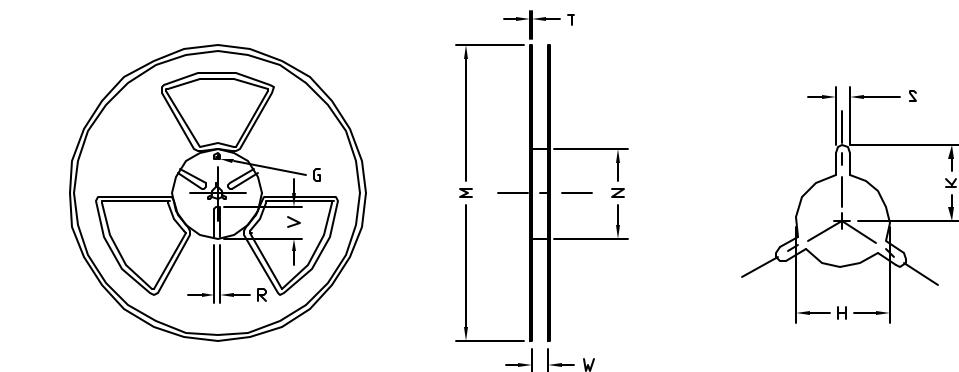
TO-252 (DPAK) Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252(DPAK) <16 mm>	6.90 ± 0.10	10.50 ± 0.10	2.70 ± 0.10	150 ± 0.10	1.50 MIN.	16.00 ± 0.10	1.75 ± 0.10	7.50 ± 0.10	8.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	0.30 ± 0.05

TO-252 (DPAK) Reel



UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	$\varnothing 330$	$\varnothing 330.00$ ± 0.10	99.50 ± 0.10	17.50 ± 0.50	2.30	$\varnothing 13.50$ ± 0.10	10.60	2.50 ± 0.10	---	---	---

TO-252 (DPAK)

Leader / Trailer
& Orientation

